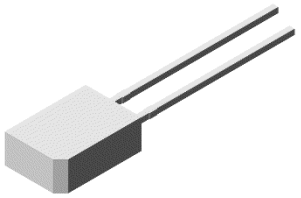
Rectangular Silicon Photodiode

OD T638

Features

- High radiant sensitive
- Low junction capacitance
- Wide radiant sensitive area
- Fast respond speed.
- Pb free
- Lens in water clear



Applications

- Industrial electronics
- Measurement
- Control circuit
- Interrupter

RoHS

Pb
pb-free

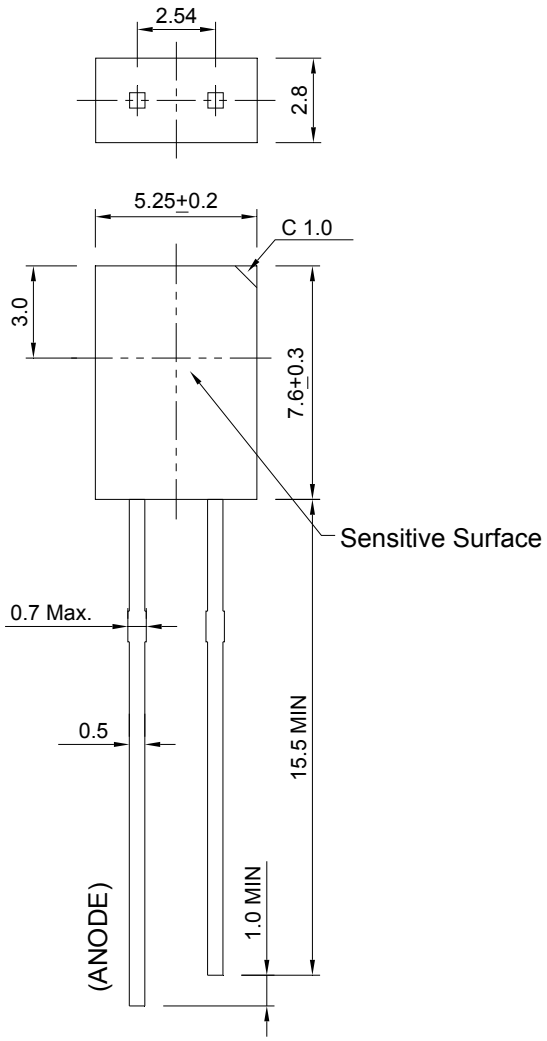
Absolute Maximum Rating at Ta =25℃,unless otherwise specified

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	32	V
Power Dissipation	Pv	150	mW
Operating Temperature Range	T_{amb}	-30 to + 85	℃
Storage Temperature	T_{stg}	-40 to + 85	℃
Soldering Temperature	T_{sd}	260+/-5 for 5 sec	℃

Note: Please take note the Absolute Maximum Rating values. Any operation beyond the specified ratings in this table will result degradation of LED life- span and may cause LED to fail.

Package Dimension:

unit: mm



Notes:

1. All dimensions are millimeters.
2. Tolerance is ± 0.2mm unless otherwise specified.
3. Specifications are subject to change without notice.

Optical Characteristics at Ta=25℃,unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Open Circuit Voltage	Ee = 5mW/cm^2 λp= 940nm	Voc	---	0.35	---	V
Short Circuit Current		Isc	---	145	---	μA
Dark Current	Ee = 0mW/cm^2 V_R = 10V	I_D	---	5	30	nA
Reverse Light Current	Ee = 5mW/cm^2 λp= 940nm V_R = 5V	I_L	---	150	---	μA
Total Capacitance	Ee = 0mW/cm^2 V_R = 3V f=1MHz	Ct	---	25	---	pF
Reverse Breakdown Voltage	Ee = 0mW/cm^2 I_R=100 μA	BV_R	33	170	---	V
Range of Spectral Bandwidth	---	$\lambda_{0.5}$	400	---	1200	nm
Wavelength of Peak Sensitivity	---	λ_p	---	980	---	nm
Rise Time	V_R=10V, R_L=1000Ω	tr	---	50	---	nS
Fall Time		tf		50	---	

Optical Characteristics Curves